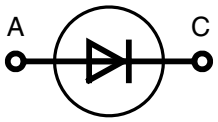
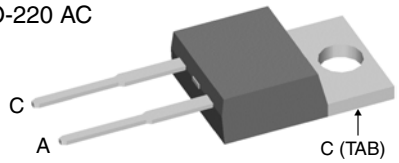
HiPerFRED™ Epitaxial Diode
with soft recovery

I_{FAV} = 15 A
V_{RRM} = 1200 V
t_{rr} = 35 ns

V_{RSM} V	V_{RRM} V	Type
1200	1200	DSEP 12-12B



TO-220 AC



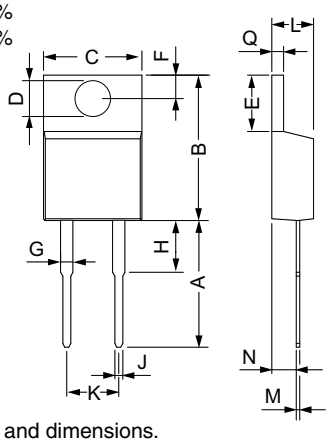
A = Anode, C = Cathode, TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		35	A
I_{FAVM}	T_C = 120°C; rectangular, d = 0.5	15	A
I_{FSM}	T_{VJ} = 45°C; tp = 10 ms (50 Hz), sine	90	A
E_{AS}	T_{VJ} = 25°C; non-repetitive I_{AS} = 9 A; L = 180 µH	8.7	mJ
I_{AR}	$V_A = 1.25 \cdot V_R$ typ.; f = 10 kHz; repetitive	0.9	A
T_{VJ}		-55...+175	°C
T_{VJM}		175	°C
T_{stg}		-55...+150	°C
P_{tot}	T_C = 25°C	95	W
M_d	mounting torque	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions		Characteristic Values typ.	max.	
I_R ①	$V_R = V_{RRM}$	T_{VJ} = 25°C		100	µA
	$V_R = V_{RRM}$	T_{VJ} = 150°C		0.5	mA
V_F ②	I_F = 15 A	T_{VJ} = 150°C		2.20	V
		T_{VJ} = 25°C		3.25	V
R_{thJC}				1.6	K/W
R_{thCH}			0.5		K/W
t_{rr}	I_F = 1 A; V_R = 30 V; -di/dt = 100 A/µs	T_{VJ} = 25°C	35		ns
I_{RM}	I_F = 25 A; V_R = 100 V; $-di_F/dt$ = 100 A/µs	T_{VJ} = 25°C	3.7		A

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0%
② Pulse Width = 300 µs, Duty Cycle < 2.0%

Data according to IEC 60747 and per diode unless otherwise specified.



Features
- International standard package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM}-values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

Applications
- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	12.7	14.73	0.5	0.58
B	14.23	16.51	0.56	0.65
C	9.66	10.66	0.38	0.42
D	3.54	4.08	0.139	0.161
E	5.85	6.85	2.3	0.42
F	2.54	3.42	0.1	0.135
G	1.15	1.77	0.045	0.07
H	-	6.35	-	0.25
J	0.64	0.89	0.025	0.035
K	4.83	5.33	0.19	0.21
L	3.56	4.82	0.14	0.19
M	0.51	0.76	0.02	0.03
N	2.04	2.49	0.08	0.115
Q	0.64	1.39	0.025	0.055

IXYS reserves the right to change limits, test conditions and dimensions.

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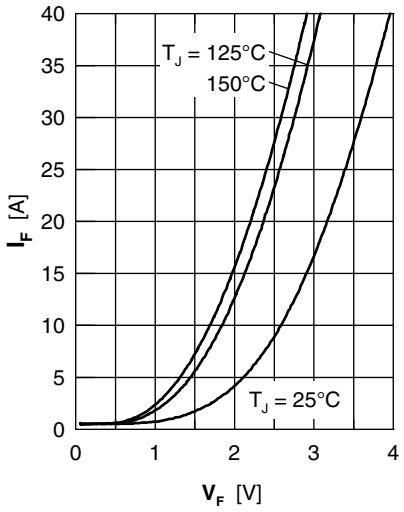

Fig.1 Forward current I_F versus V_F

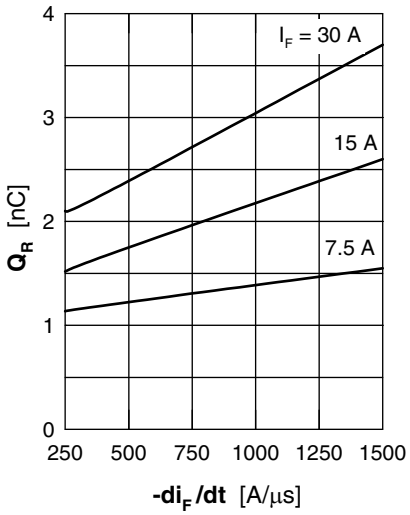

Fig.2 Typ. reverse recovery charge Q_{rr} versus -di$_F$/dt

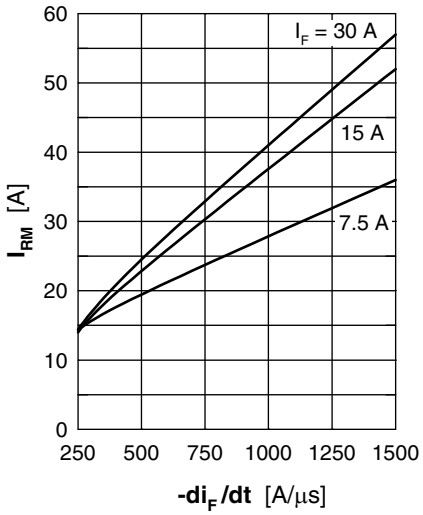

Fig. 3 Typ. peak reverse current I_{RM} versus -di$_F$/dt

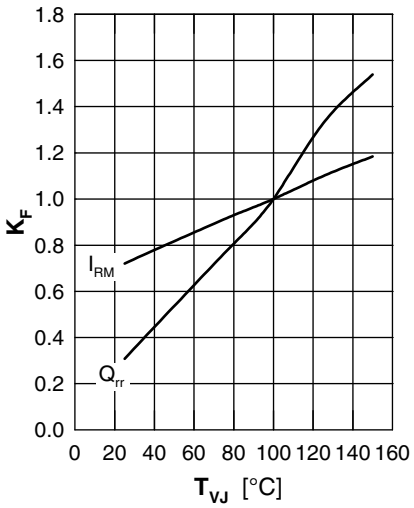

Fig.4 Dynamic parameters Q_{RR}, I_{RM} versus T_{VJ}

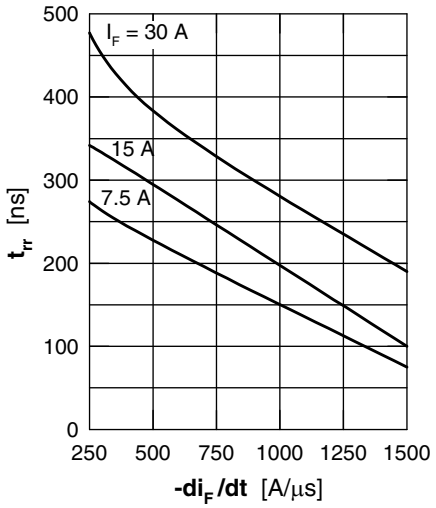

Fig. 5 Typ. recovery time t_{rr} versus -di$_F$/dt

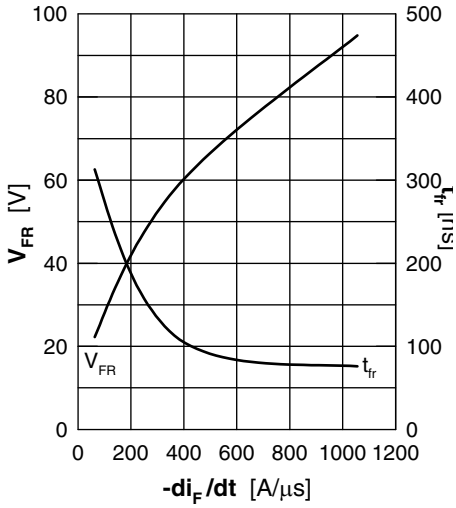

Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus -di$_F$/dt

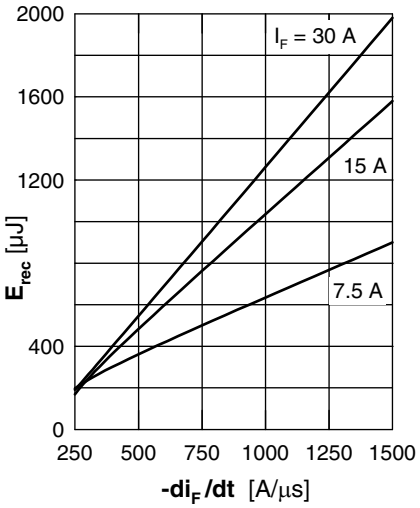

Fig. 7 Typ. recovery energy E_{rec} versus -di$_F$/dt

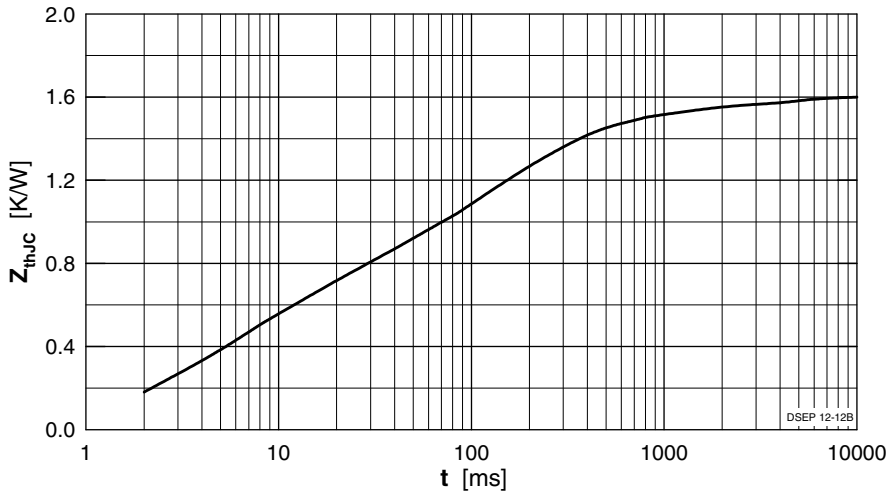

Fig. 8 Transient thermal resistance junction to case